



CS10N15 A3

General Description:

CS10N15 A3, the silicon N-channel Enhanced VDMOSFETs, is obtained by the high density Trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-251, which accords with the RoHS standard..

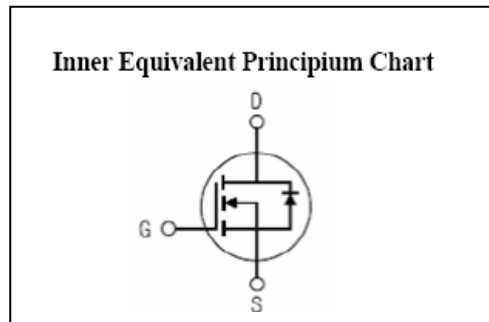
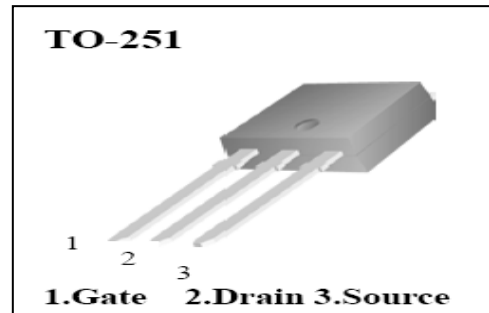
Features:

- Fast Switching
- Low ON Resistance ($R_{dson} \leq 300m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Applications:

Power switch circuit of adaptor and charger.

V_{DSS}	150	V
I_D	10	A
P_D	36.7	W
$R_{DS(ON)Typ}$	230	m Ω



Absolute (T_c= 25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	150	V
I_D	Continuous Drain Current	10	A
	Continuous Drain Current T _c = 100 °C	6.0	A
I_{DM}^{a1}	Pulsed Drain Current	40	A
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}^{a2}	Avalanche Energy ,Repetitive	17.4	mJ
I_{AS}^{a2}	Avalanche Current	5.9	A
P_D	Power Dissipation	36.7	W
	Derating Factor above 25 °C	0.294	W/°C
T _J , T _{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	°C
T _L	Maximum Temperature for Soldering	300	°C

Electrical Characteristics (T_J= 25°C unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250 μA	150	--	--	V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 150V, V _{GS} = 0V, T _a = 25°C	--	--	1	μA
		V _{DS} = 120V, V _{GS} = 0V, T _a = 125°C	--	--	100	
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} =20V	--	--	100	nA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} = -20V	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =2.0A	--	230	300	mΩ
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =4.5V, I _D =1.0A	--	250	330	mΩ
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	1.7	2.3	2.8	V
Pulse width tp ≤ 300 μs, δ ≤ 2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	--	3.5	--	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V V _{DS} = 75V f = 1.0MHz	--	549.5	--	pF
C _{oss}	Output Capacitance		--	22.5	--	
C _{rss}	Reverse Transfer Capacitance		--	11.4	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	V _{GS} =10V, R _G =6Ω, V _{DD} =75V, I _D =2A	--	8.1	--	ns
t _r	Rise Time		--	6.4	--	
t _{d(OFF)}	Turn-Off Delay Time		--	31.2	--	
t _f	Fall Time		--	19.3	--	
Q _{g(4.5V)}	Total Gate Charge	V _{DD} =75V, I _D =2A V _{GS} =10V	--	5.9	--	nC
Q _{g(10V)}	Total Gate Charge		--	11.6	--	
Q _{gs}	Gate to Source Charge		--	2	--	
Q _{gd}	Gate to Drain ("Miller") Charge		--	2.6	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	2	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	8	A
V_{SD}	Diode Forward Voltage	$I_S=2.0A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=2.0A, T_J = 25^\circ C$	--	57.1	--	ns
Q_{rr}	Reverse Recovery Charge	$dI_F/dt=100A/us, V_{GS}=0V$	--	87.9	--	nC
Pulse width $t_p \leq 300 \mu s, \delta \leq 2\%$						

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Junction-to-Case	3.4	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	100	$^\circ C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=1.0mH, I_D=5.9A, \text{Start } T_J=25^\circ C$

Characteristics Curve:

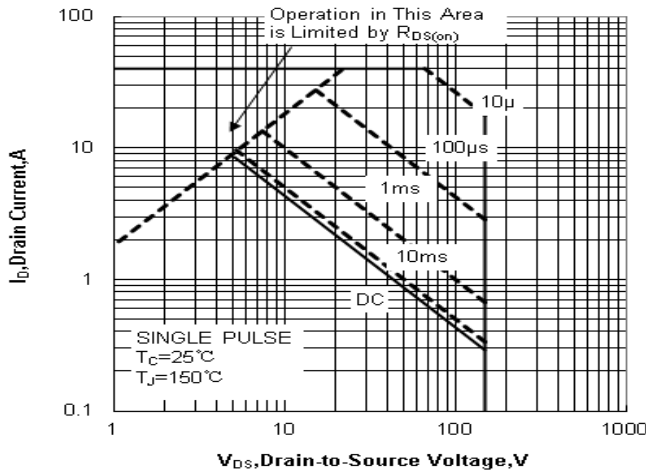


Figure 1 Maximum Forward Bias Safe Operating Area

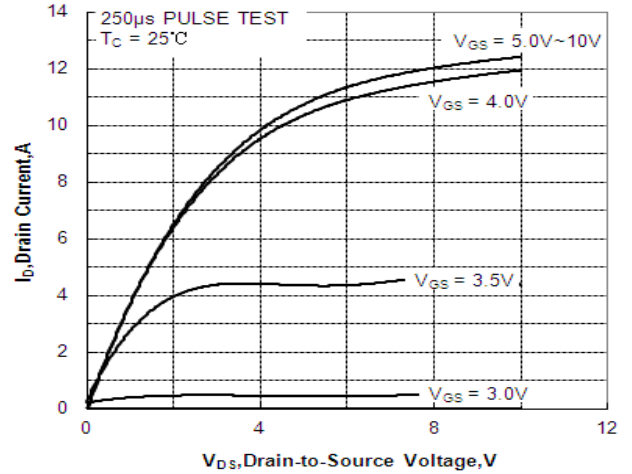


Figure 2 Typical Output Characteristics

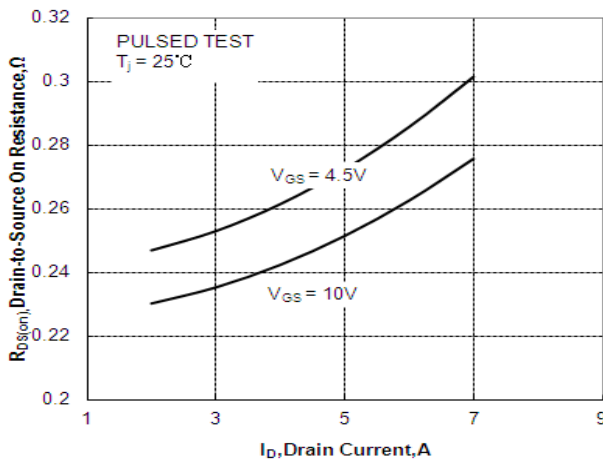


Figure 3 Typical Drain to Source ON Resistance vs Drain Current

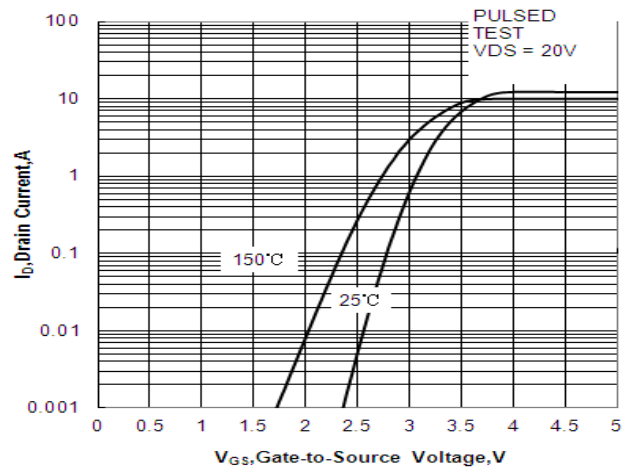


Figure 4 Typical Transfer Characteristics

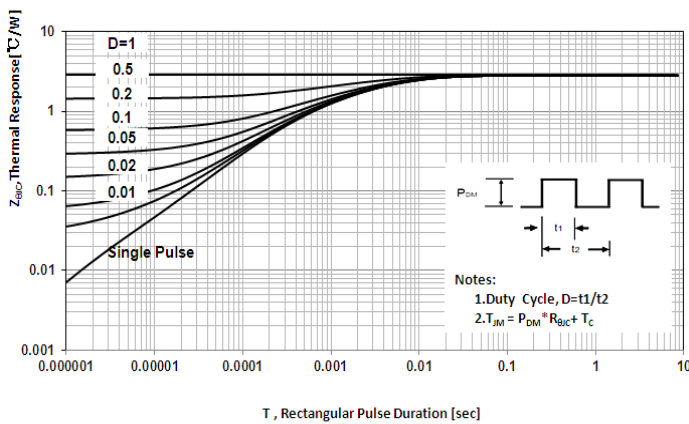


Figure 5 Maximum Effective Thermal Impedance, Junction to Case

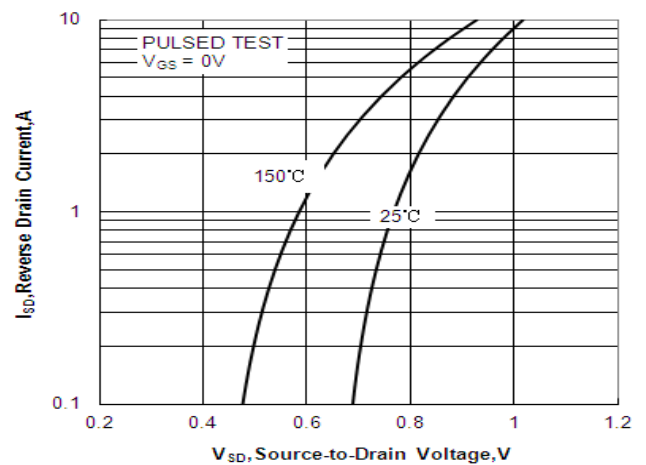


Figure 6 Body Diode Forward Voltage vs Source Current and Temperature

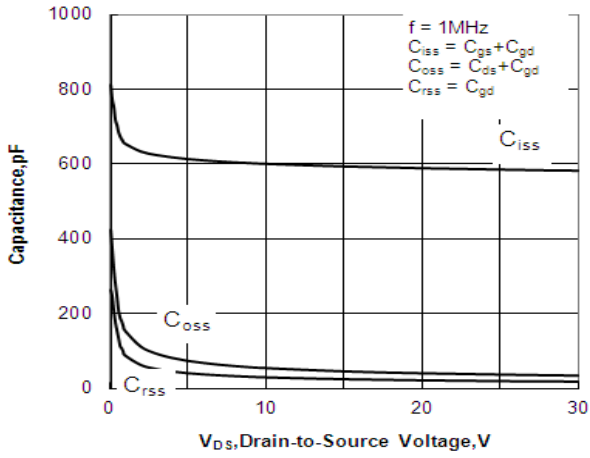


Figure 7 Typical Capacitance vs Drain to Source Voltage

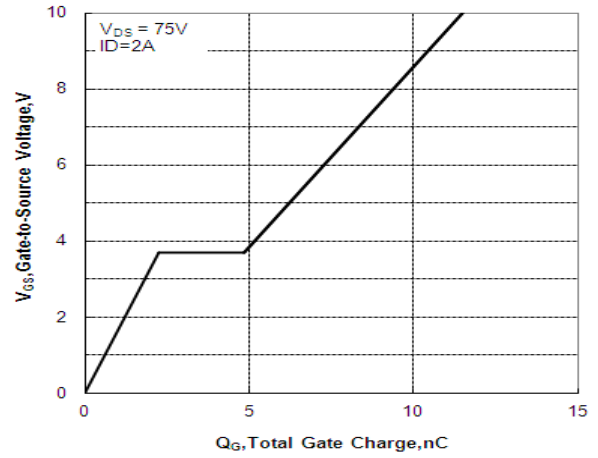


Figure 8 Typical Gate Charge vs Gate to Source Voltage

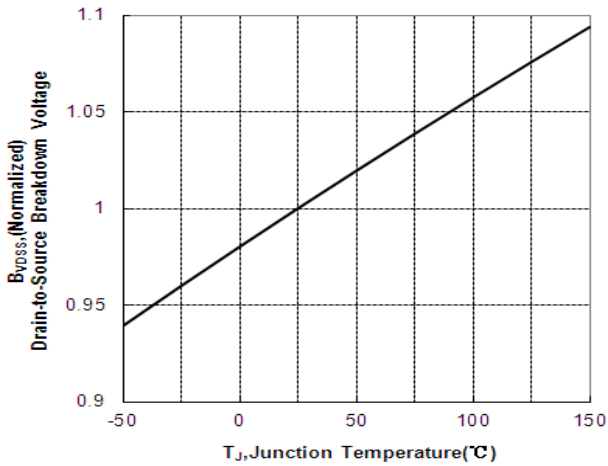


Figure 9 Typical Breakdown Voltage vs Junction Temperature

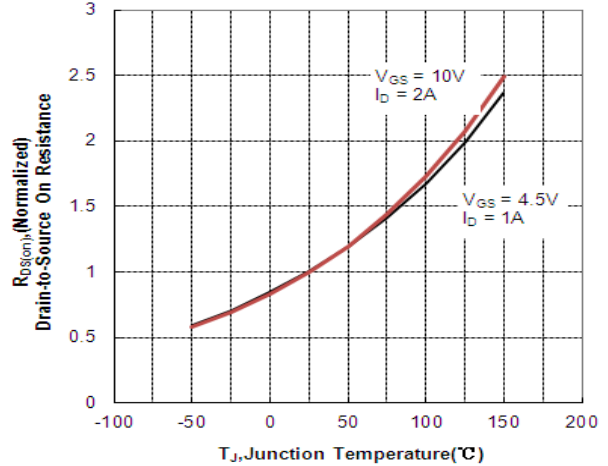


Figure 10 Typical Drain to Source on Resistance vs Junction Temperature

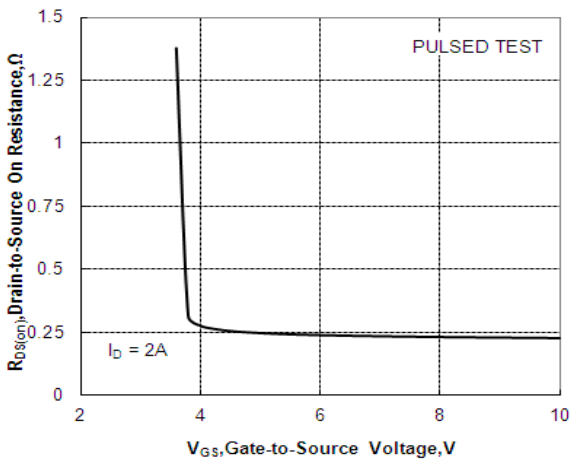


Figure 11 Drain-to-Source On Resistance vs Gate Voltage and Drain Current

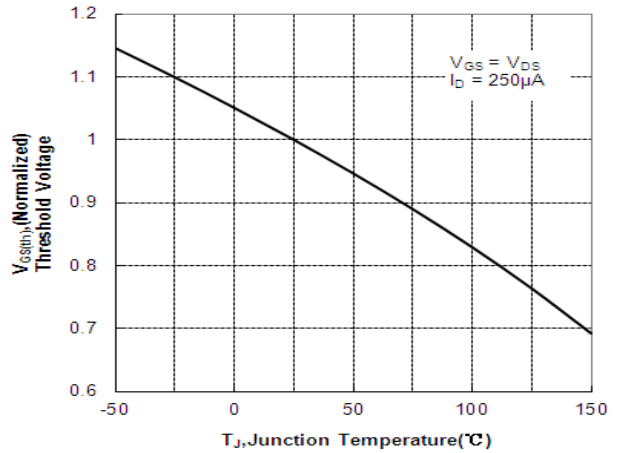


Figure 12 Typical Threshold Voltage vs Junction Temperature

Test Circuit and Waveform

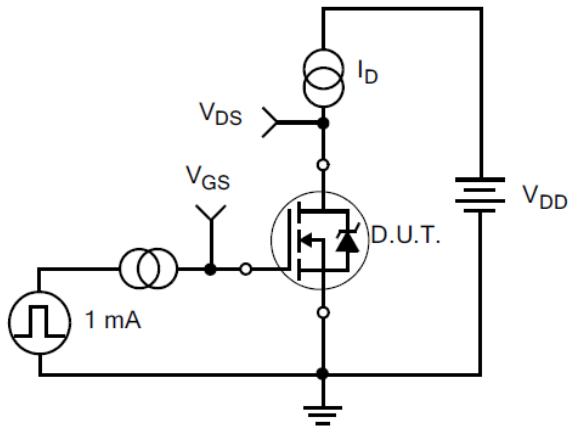


Figure 14. Gate Charge Test Circuit

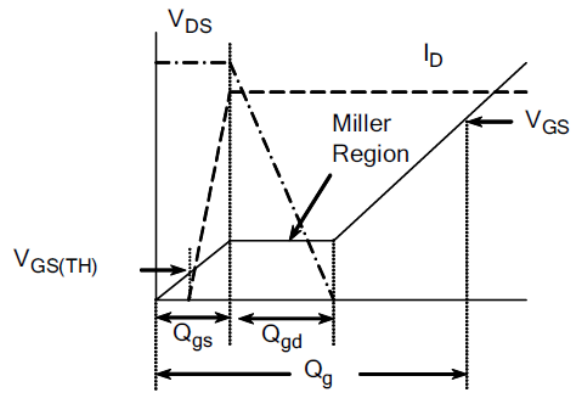


Figure 15. Gate Charge Waveforms

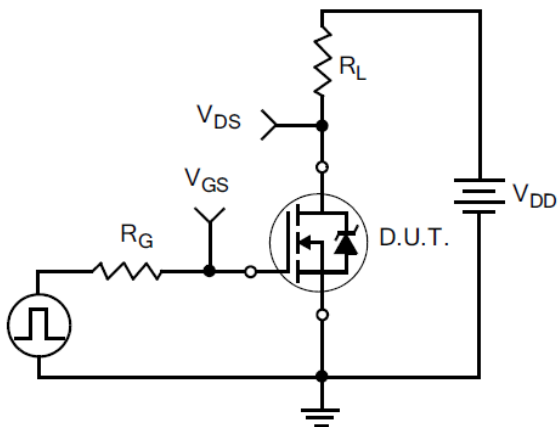


Figure 16. Resistive Switching Test Circuit

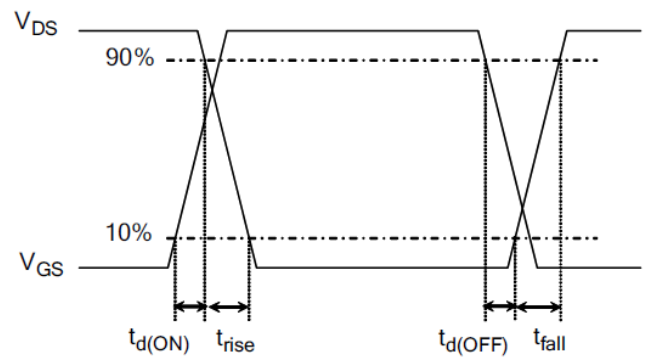


Figure 17. Resistive Switching Waveforms

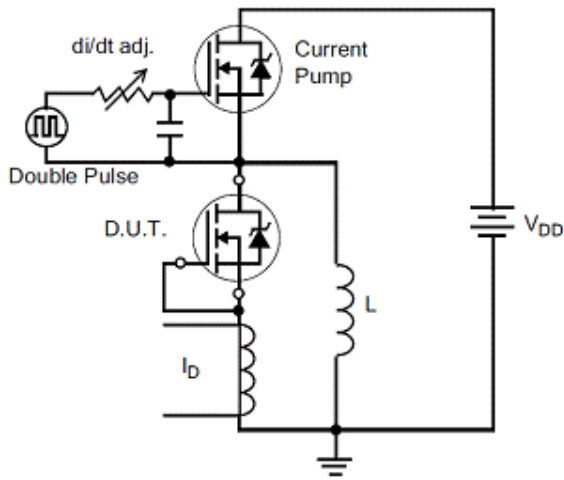


Figure 18. Diode Reverse Recovery Test Circuit

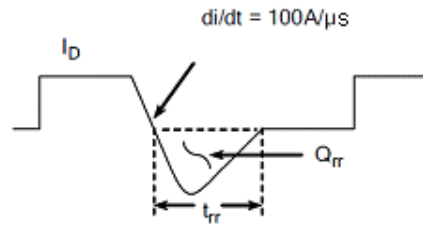


Figure 19. Diode Reverse Recovery Waveform

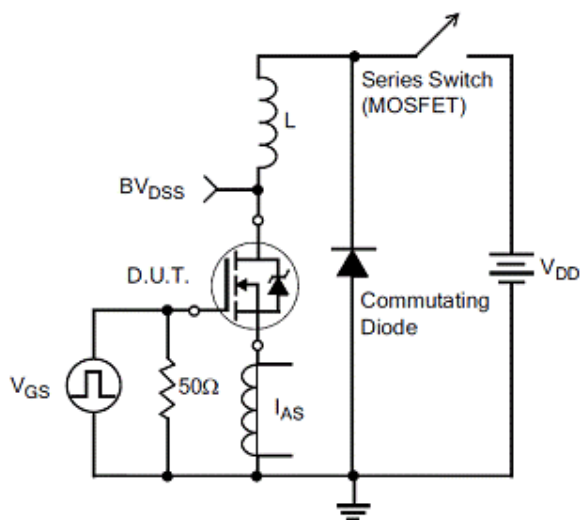


Figure 20. Unclamped Inductive Switching Test Circuit

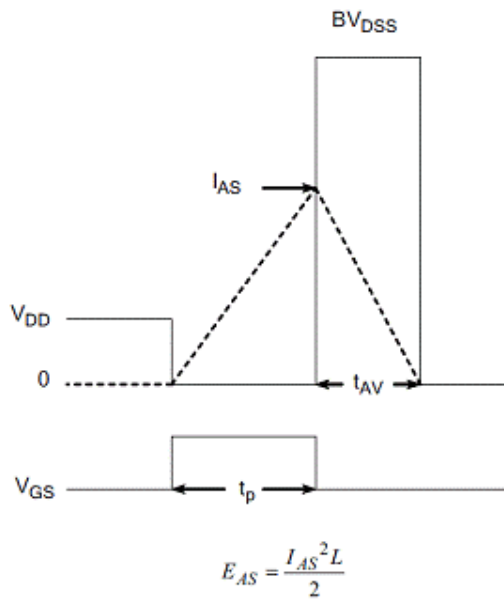
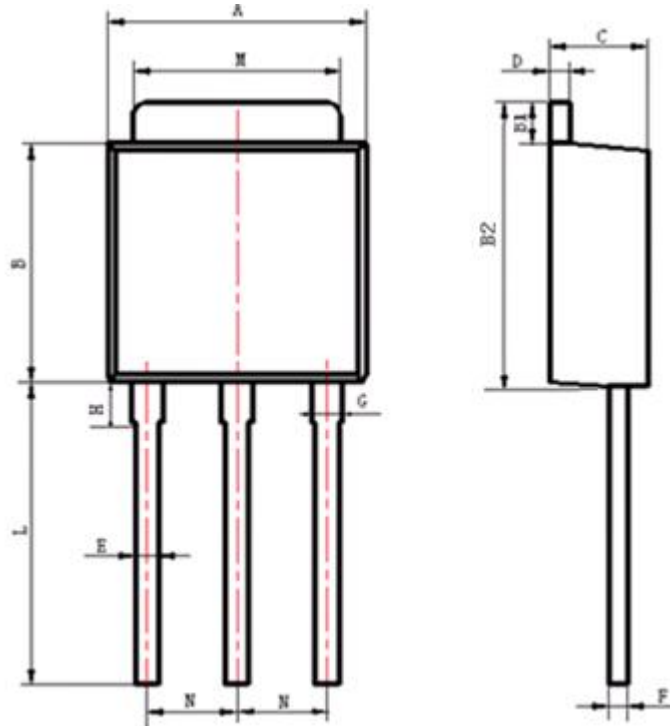


Figure 21. Unclamped Inductive Switching Waveform

Package Information:



Items	Values(mm)	
	MIN	MAX
A	6.30	6.90
B	5.20	6.30
B1	0.70	1.30
B2	6.80	7.40
C	2.10	2.50
D	0.30	0.60
E	0.50	0.86
F	0.30	0.60
G	0.70	1.00
H	1.40	2.40
L*	7.50	9.80
M	5.10	5.50
N	2.09	2.49

*adjustable

TO-251 Package



The name and content of poisonous and harmful material in products

	Hazardous Substance									
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE	DIBP	DEHP	DBP	BBP
Limit	≤0.1%	≤0.1%	≤0.01%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%
Lead Frame	○	○	○	○	○	○	○	○	○	○
Molding	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○	○	○	○	○
Solder	×	○	○	○	○	○	○	○	○	○
Note	<p>○: Means the hazardous material is under the criterion of 2011/65/EU. ×: Means the hazardous material exceeds the criterion of 2011/65/EU. The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's RoHS.</p>									

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. VDMOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by Huajing Microelectronics and subject to regular change without notice.

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